
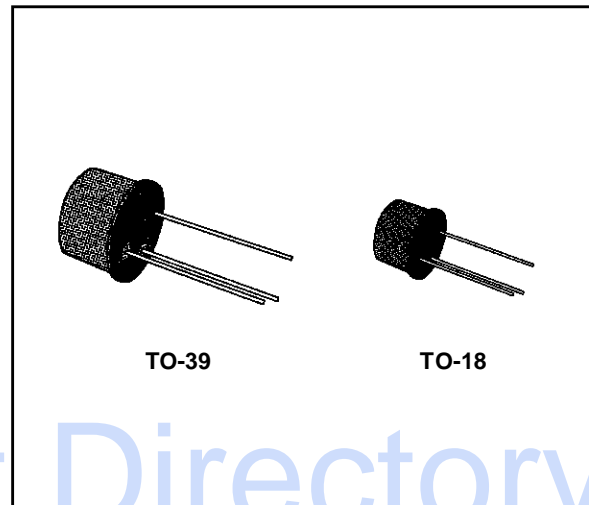


**HIGH SPEED SWITCHES**

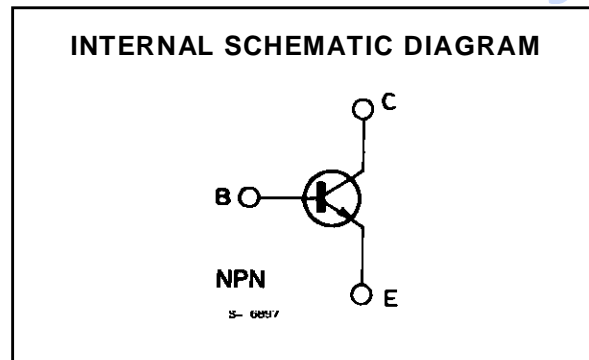
**DESCRIPTION**

The 2N2218A, 2N2219A, 2N2221A and 2N2222A are silicon planar epitaxial NPN transistors in Jedec TO-39 (for 2N2218A and 2N2219A) and in Jedec TO-18 (for 2N2221A and 2N2222A) metal cases. They are designed for high-speed switching applications at collector currents up to 500 mA, and feature useful current gain over a wide range of collector current, low leakage currents and low saturation voltages.

 2N2218A/2N2219A approved to CECC 50002-100, 2N2221A/2N2222A approved to CECC 50002-101 available on request.



Datasheet Directory



**ABSOLUTE MAXIMUM RATINGS**

| Symbol    | Parameter   | Value       | Unit       |
|-----------|---|-------------|------------|
| $V_{CBO}$ | Collector-base Voltage ( $I_E = 0$ )  | 75          | V          |
| $V_{CEO}$ | Collector-emitter Voltage ( $I_B = 0$ )   | 40          | V          |
| $V_{EBO}$ | Emitter-base Voltage ( $I_C = 0$ )  | 6           | V          |
| $I_C$     | Collector Current   | 0.8         | A          |
| $P_{tot}$ | Total Power Dissipation at $T_{amb} \leq 25^\circ C$<br>for <b>2N2218A</b> and <b>2N2219A</b><br>for <b>2N2221A</b> and <b>2N2222A</b><br>at $T_{case} \leq 25^\circ C$<br>for <b>2N2218A</b> and <b>2N2219A</b><br>for <b>2N2221A</b> and <b>2N2222A</b> | 0.8         | W          |
|           |   | 0.5         | W          |
|           |   | 3           | W          |
|           |   | 1.8         | W          |
| $T_{stg}$ | Storage Temperature   | - 65 to 200 | $^\circ C$ |
| $T_j$     | Junction Temperature  | 175         | $^\circ C$ |

## 2N2218A-2N2219A-2N2221A-2N2222A

### THERMAL DATA

|                  |                                     |     | 2N2218A<br>2N2219A | 2N2221A<br>2N2222A |
|------------------|-------------------------------------|-----|--------------------|--------------------|
| $R_{th\ j-case}$ | Thermal Resistance Junction-case    | Max | 50 °C/W            | 83.3 °C/W          |
| $R_{th\ j-amb}$  | Thermal Resistance Junction-ambient | Max | 187.5 °C/W         | 300 °C/W           |

### ELECTRICAL CHARACTERISTICS ( $T_{amb} = 25\text{ °C}$ unless otherwise specified)

| Symbol            | Parameter  | Test Conditions                                  | Min. | Typ. | Max. | Unit          |
|-------------------|--|--|------|------|------|---------------|
| $I_{CBO}$         | Collector Cutoff Current<br>( $I_E = 0$ )              | $V_{CB} = 60\text{ V}$                           |      |      | 10   | nA            |
|                   |  | $V_{CB} = 60\text{ V}$ $T_{amb} = 150\text{ °C}$ |      |      | 10   | $\mu\text{A}$ |
| $I_{CEX}$         | Collector Cutoff Current<br>( $V_{BE} = -3\text{ V}$ ) | $V_{CE} = 60\text{ V}$                           |      |      | 10   | nA            |
| $I_{EBO}$         | Emitter Cutoff Current<br>( $I_C = 0$ )                | $V_{EB} = 3\text{ V}$                            |      |      | 10   | nA            |
| $I_{BEX}$         | Base Cutoff Current<br>( $V_{BE} = -3\text{ V}$ )      | $V_{CE} = 60\text{ V}$                           |      |      | 20   | nA            |
| $V_{(BR)\ CBO}$   | Collector-base Breakdown<br>Voltage ( $I_E = 0$ )      | $I_C = 10\ \mu\text{A}$                          | 75   |      |      | V             |
| $V_{(BR)\ CEO}^*$ | Collector-emitter Breakdown<br>Voltage ( $I_B = 0$ )   | $I_C = 10\text{ mA}$                             | 40   |      |      | V             |
| $V_{(BR)\ EBO}$   | Emitter-base Breakdown<br>Voltage ( $I_C = 0$ )        | $I_E = 10\ \mu\text{A}$                          | 6    |      |      | V             |
| $V_{CE(sat)}^*$   | Collector-emitter Saturation<br>Voltage                | $I_C = 150\text{ mA}$ $I_B = 15\text{ mA}$       |      |      | 0.3  | V             |
|                   |  | $I_C = 500\text{ mA}$ $I_B = 50\text{ mA}$       |      |      | 1    | V             |
| $V_{BE(sat)}^*$   | Base-emitter Saturation<br>Voltage                     | $I_C = 150\text{ mA}$ $I_B = 15\text{ mA}$       | 0.6  |      | 1.2  | V             |
|                   |  | $I_C = 500\text{ mA}$ $I_B = 50\text{ mA}$       |      |      | 2    | V             |
| $h_{FE}^*$        | DC Current Gain  | for <b>2N2218A</b> and <b>2N2221A</b>            |      |      |      |               |
|                   |  | $I_C = 0.1\text{ mA}$ $V_{CE} = 10\text{ V}$     | 20   |      |      |               |
|                   |  | $I_C = 1\text{ mA}$ $V_{CE} = 10\text{ V}$       | 25   |      |      |               |
|                   |  | $I_C = 10\text{ mA}$ $V_{CE} = 10\text{ V}$      | 35   |      |      |               |
|                   |  | $I_C = 150\text{ mA}$ $V_{CE} = 10\text{ V}$     | 40   |      | 120  |               |
|                   |  | $I_C = 500\text{ mA}$ $V_{CE} = 10\text{ V}$     | 25   |      |      |               |
|                   |  | $I_C = 150\text{ mA}$ $V_{CE} = 1\text{ V}$      | 20   |      |      |               |
|                   |  | $I_C = 10\text{ mA}$ $V_{CE} = 10\text{ V}$      | 15   |      |      |               |
| $h_{FE}^*$        | DC Current Gain  | for <b>2N2219A</b> and <b>2N2222A</b>            |      |      |      |               |
|                   |  | $I_C = 0.1\text{ mA}$ $V_{CE} = 10\text{ V}$     | 35   |      |      |               |
|                   |  | $I_C = 1\text{ mA}$ $V_{CE} = 10\text{ V}$       | 50   |      |      |               |
|                   |  | $I_C = 10\text{ mA}$ $V_{CE} = 10\text{ V}$      | 75   |      |      |               |
|                   |  | $I_C = 150\text{ mA}$ $V_{CE} = 10\text{ V}$     | 100  |      | 300  |               |
|                   |  | $I_C = 500\text{ mA}$ $V_{CE} = 10\text{ V}$     | 40   |      |      |               |
|                   |  | $I_C = 150\text{ mA}$ $V_{CE} = 1\text{ V}$      | 50   |      |      |               |
|                   |  | $I_C = 10\text{ mA}$ $V_{CE} = 10\text{ V}$      | 35   |      |      |               |
|                   | $T_{amb} = -55\text{ °C}$                              |  |      |      |      |               |

\* Pulsed : pulse duration = 300  $\mu\text{s}$ , duty cycle = 1 %.

ELECTRICAL CHARACTERISTICS (continued)

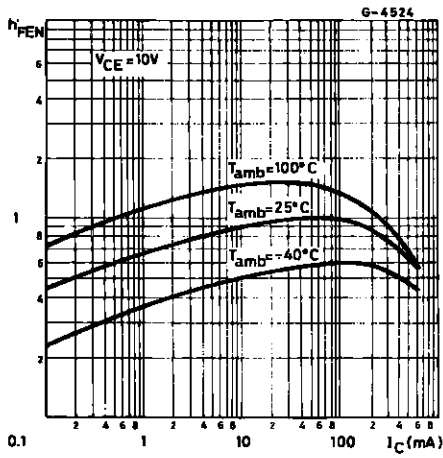
| Symbol                 | Parameter                    | Test Conditions   | Min.                  | Typ. | Max.   | Unit   |
|------------------------|------------------------------|---|-----------------------|------|--|--|
| $h_{fe}$               | Small Signal Current Gain    | $I_C = 1 \text{ mA}$ $V_{CE} = 10 \text{ V}$<br>$f = 1 \text{ kHz}$<br>for <b>2N2218A</b> and <b>2N2221A</b><br>for <b>2N2219A</b> and <b>2N2222A</b><br>$I_C = 10 \text{ mA}$ $V_{CE} = 10 \text{ V}$<br>$f = 1 \text{ kHz}$<br>for <b>2N2218A</b> and <b>2N2221A</b><br>for <b>2N2219A</b> and <b>2N2222A</b> | 30<br>50<br>50<br>75  |      | 150<br>300<br>300<br>375   |  |
| $f_T$                  | Transition Frequency         | $I_C = 20 \text{ mA}$ $V_{CE} = 20 \text{ V}$<br>$f = 100 \text{ MHz}$<br>for <b>2N2218A</b> and <b>2N2221A</b><br>for <b>2N2219A</b> and <b>2N2222A</b>  | 250<br>300            |      |  | MHz<br>MHz   |
| $C_{EBO}$              | Emitter-base Capacitance     | $I_C = 0$<br>$f = 100 \text{ kHz}$ $V_{EB} = 0.5 \text{ V}$   |                       |      | 25   | pF   |
| $C_{CBO}$              | Collector-base Capacitance   | $I_E = 0$<br>$f = 100 \text{ kHz}$ $V_{CB} = 10 \text{ V}$  |                       |      | 8  | pF   |
| $R_{e(hie)}$           | Real Part of Input Impedance | $I_C = 20 \text{ mA}$<br>$f = 300 \text{ MHz}$ $V_{CE} = 20 \text{ V}$  |                       |      | 60   | $\Omega$   |
| NF                     | Noise Figure                 | $I_C = 100 \mu\text{A}$ $V_{CE} = 10 \text{ V}$<br>$R_g = 1 \text{ k}\Omega$ $f = 1 \text{ kHz}$  |                       | 4    |  | dB   |
| $h_{ie}^{**}$          | Input Impedance              | $I_C = 1 \text{ mA}$ $V_{CE} = 10 \text{ V}$<br>for <b>2N2218A</b> and <b>2N2221A</b><br>for <b>2N2219A</b> and <b>2N2222A</b><br>$I_C = 10 \text{ mA}$ $V_{CE} = 10 \text{ V}$<br>for <b>2N2218A</b> and <b>2N2221A</b><br>for <b>2N2219A</b> and <b>2N2222A</b>   | 1<br>2<br>0.2<br>0.25 |      | 3.5<br>8<br>1<br>1.25  | $\Omega$<br>$\Omega$<br>$\Omega$<br>$\Omega$                     |
| $h_{re}^{**}$          | Reverse Voltage Ratio        | $I_C = 1 \text{ mA}$ $V_{CE} = 10 \text{ V}$<br>for <b>2N2218A</b> and <b>2N2221A</b><br>for <b>2N2219A</b> and <b>2N2222A</b><br>$I_C = 10 \text{ mA}$ $V_{CE} = 10 \text{ V}$<br>for <b>2N2218A</b> and <b>2N2221A</b><br>for <b>2N2219A</b> and <b>2N2222A</b>   |                       |      | $5 \times 10^{-4}$<br>$8 \times 10^{-4}$<br>$2.5 \times 10^{-4}$<br>$4 \times 10^{-4}$ |  |
| $h_{oe}^{**}$          | Output Admittance            | $I_C = 1 \text{ mA}$ $V_{CE} = 10 \text{ V}$<br>for <b>2N2218A</b> and <b>2N2221A</b><br>for <b>2N2219A</b> and <b>2N2222A</b><br>$I_C = 10 \text{ mA}$ $V_{CE} = 10 \text{ V}$<br>for <b>2N2218A</b> and <b>2N2221A</b><br>for <b>2N2219A</b> and <b>2N2222A</b>   | 3<br>5<br>10<br>25    |      | 15<br>35<br>100<br>200   | $\mu\text{S}$<br>$\mu\text{S}$<br>$\mu\text{S}$<br>$\mu\text{S}$ |
| $t_d^{***}$            | Delay Time                   | $I_C = 150 \text{ mA}$ $V_{CC} = 30 \text{ V}$<br>$I_{B1} = 15 \text{ mA}$ $V_{BB} = -0.5 \text{ V}$  |                       |      | 10   | ns   |
| $t_r^{***}$            | Rise Time                    | $I_C = 150 \text{ mA}$ $V_{CC} = 30 \text{ V}$<br>$I_{B1} = 15 \text{ mA}$ $V_{BB} = -0.5 \text{ V}$  |                       |      | 25   | ns   |
| $t_s^{***}$            | Storage Time                 | $I_C = 150 \text{ mA}$ $V_{CC} = 30 \text{ V}$<br>$I_{B1} = -I_{B2} = 15 \text{ mA}$  |                       |      | 225  | ns   |
| $t_f^{***}$            | Fall Time                    | $I_C = 150 \text{ mA}$ $V_{CC} = 30 \text{ V}$<br>$I_{B1} = -I_{B2} = 15 \text{ mA}$  |                       |      | 60   | ns   |
| $r_{bb} \cdot C_{b'c}$ | Feedback Time Constant       | $I_C = 20 \text{ mA}$<br>$f = 31.8 \text{ MHz}$ $V_{CE} = 20 \text{ V}$   |                       |      | 150  | ps   |

\*\*  $f = 1 \text{ kHz}$

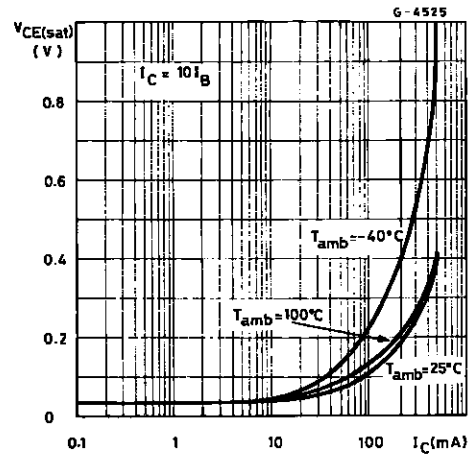
\*\*\* see test circuit.

2N2218A-2N2219A-2N2221A-2N2222A

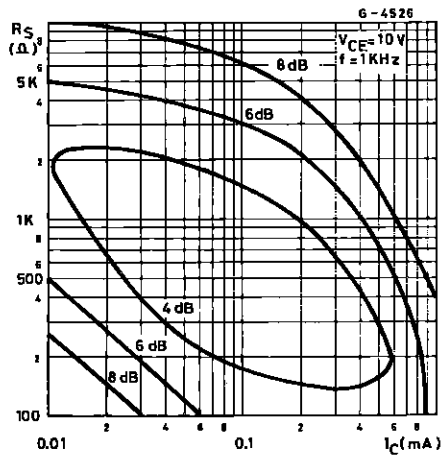
Normalized DC Current Gain.



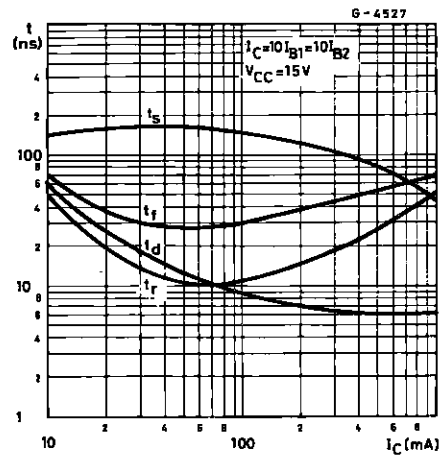
Collector-emitter Saturation Voltage.



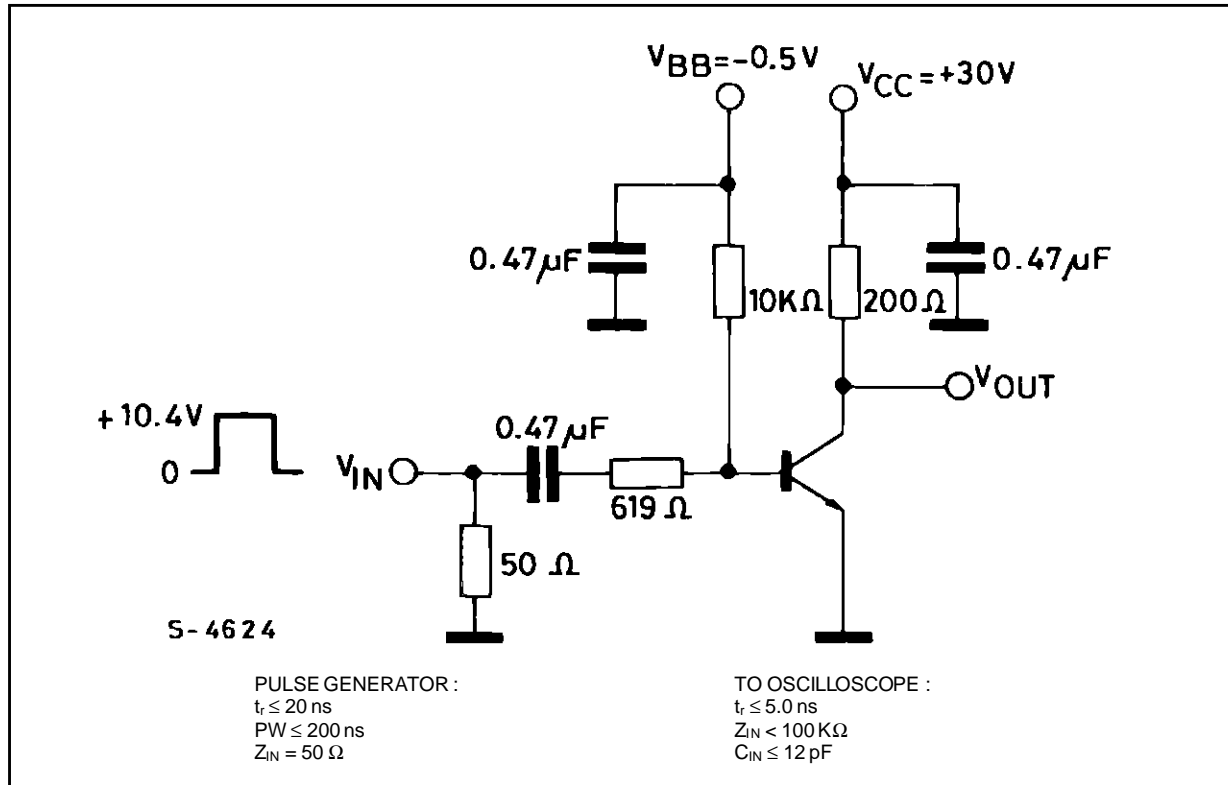
Contours of Constant Narrow Band Noise Figure.



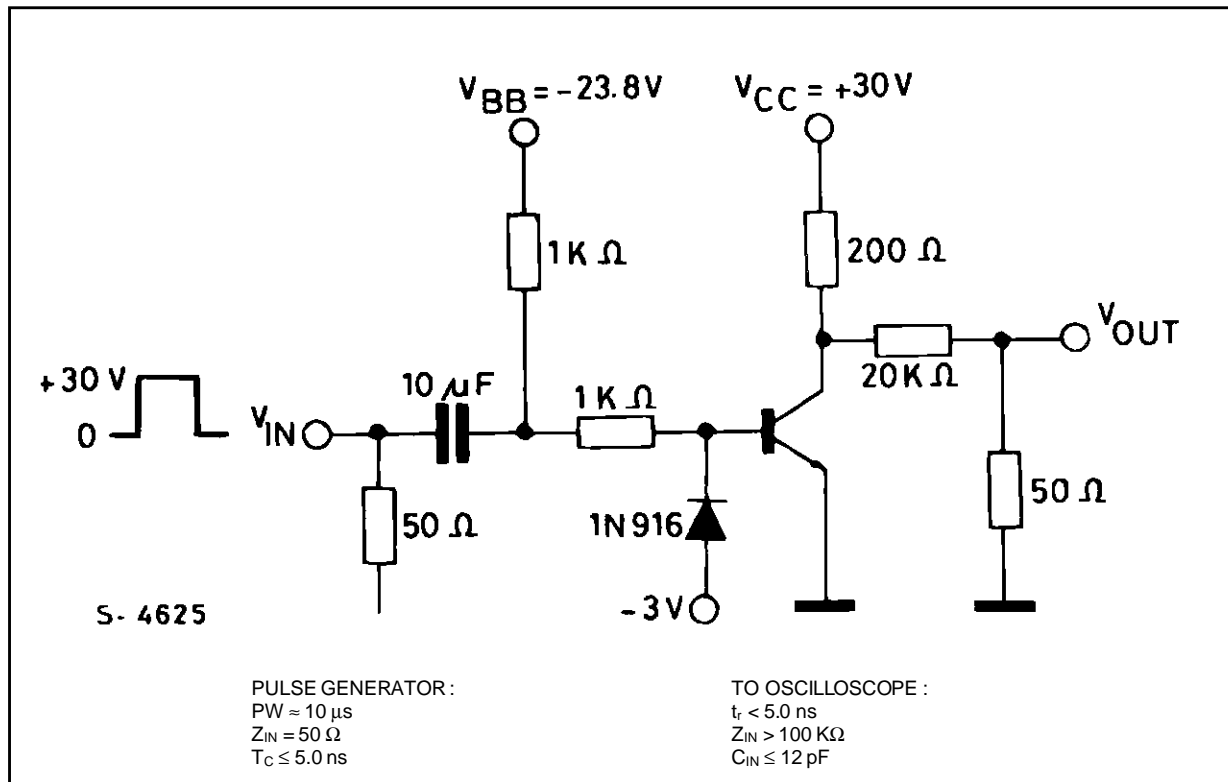
Switching Time vs. Collector Current.



Test Circuit for  $t_d$ ,  $t_r$ .

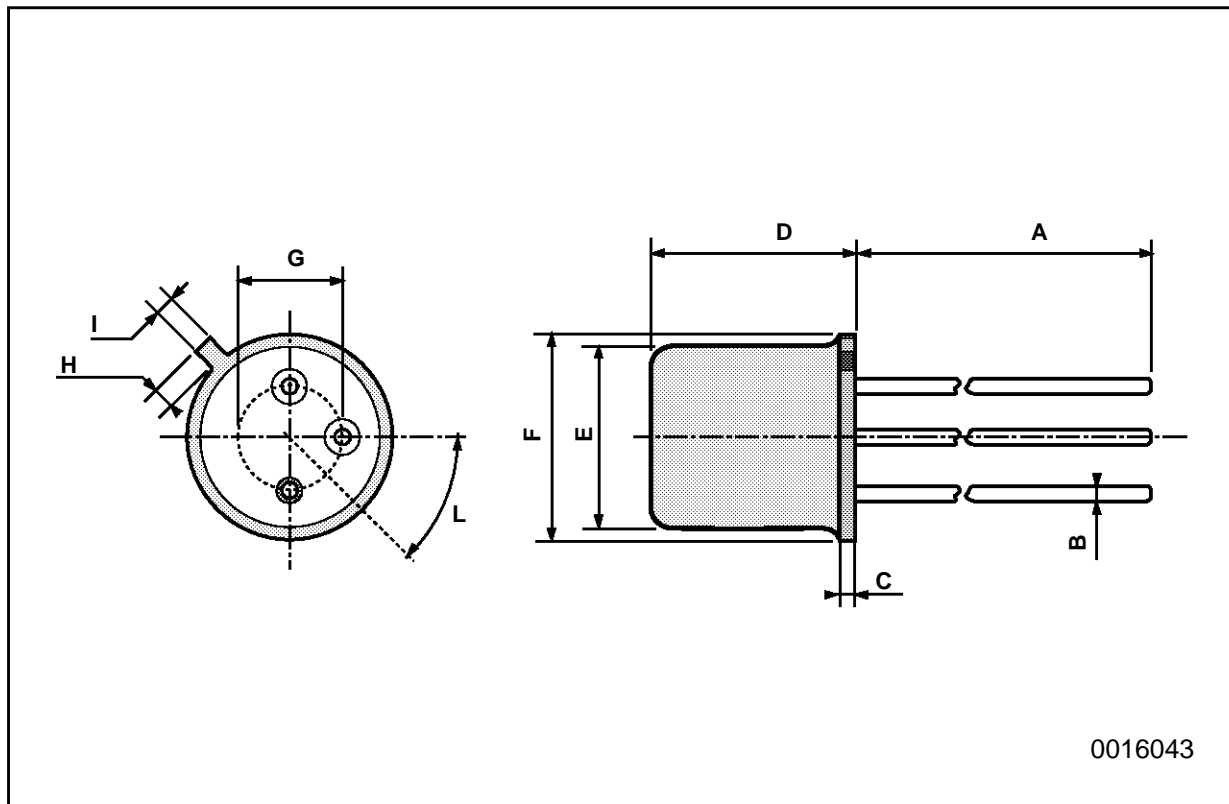


Test Circuit for  $t_d$ ,  $t_r$ .



**TO-18 MECHANICAL DATA**

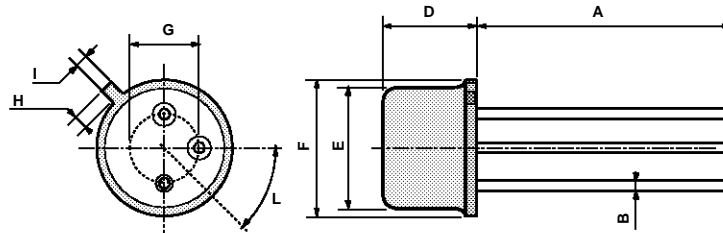
| DIM. | mm   |      |      | inch  |       |       |
|------|------|------|------|-------|-------|-------|
|      | MIN. | TYP. | MAX. | MIN.  | TYP.  | MAX.  |
| A    |      | 12.7 |      |       | 0.500 |       |
| B    |      |      | 0.49 |       |       | 0.019 |
| D    |      |      | 5.3  |       |       | 0.208 |
| E    |      |      | 4.9  |       |       | 0.193 |
| F    |      |      | 5.8  |       |       | 0.228 |
| G    | 2.54 |      |      | 0.100 |       |       |
| H    |      |      | 1.2  |       |       | 0.047 |
| I    |      |      | 1.16 |       |       | 0.045 |
| L    | 45°  |      |      | 45°   |       |       |



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**TO39 MECHANICAL DATA**

| DIM. | mm         |      |      | inch  |      |       |
|------|------------|------|------|-------|------|-------|
|      | MIN.       | TYP. | MAX. | MIN.  | TYP. | MAX.  |
| A    | 12.7       |      |      | 0.500 |      |       |
| B    |            |      | 0.49 |       |      | 0.019 |
| D    |            |      | 6.6  |       |      | 0.260 |
| E    |            |      | 8.5  |       |      | 0.334 |
| F    |            |      | 9.4  |       |      | 0.370 |
| G    | 5.08       |      |      | 0.200 |      |       |
| H    |            |      | 1.2  |       |      | 0.047 |
| I    |            |      | 0.9  |       |      | 0.035 |
| L    | 45° (typ.) |      |      |       |      |       |



P008B

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